TOSHIBA Insulated Gate Bipolar Transistor Silicon N Channel IGBT

# GT50J121

# High Power Switching Applications Fast Switching Applications

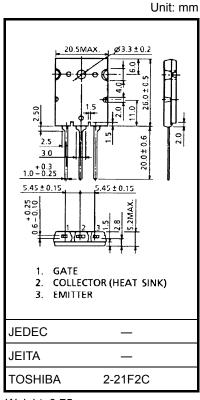
- Fourth-generation IGBT
- Enhancement mode type
- Fast switching (FS): Operating frequency up to 50 kHz (reference)
  - High speed:  $t_f = 0.05 \mu s$  (typ.)
  - Low switching loss:  $E_{on} = 1.30 \text{ mJ (typ.)}$

 $: E_{off} = 1.34 \text{ mJ (typ.)}$ 

• Low saturation Voltage:  $V_{CE (sat)} = 2.0 \text{ V (typ.)}$ 

### Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Collector-emitter voltage		V <sub>CES</sub>	600	V	
Gate-emitter voltage		V <sub>GES</sub>	±20	V	
Collector current	DC	IC	50	А	
	1 ms	I <sub>CP</sub>	100		
Collector power dissipation (Tc = 25°C)		P <sub>C</sub>	240	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-55 to 150	°C	



Weight: 9.75 g

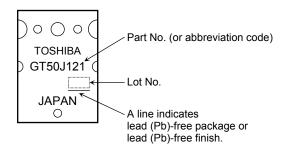
Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### **Thermal Characteristics**

Characteristics	Symbol	Max	Unit	
Thermal resistance	R <sub>th (j-c)</sub>	0.521	°C/W	

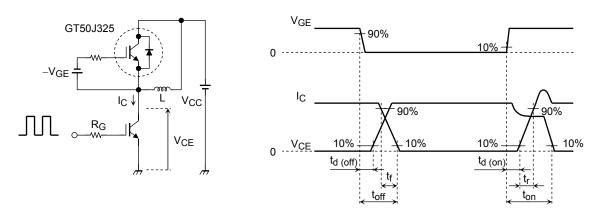
#### Marking



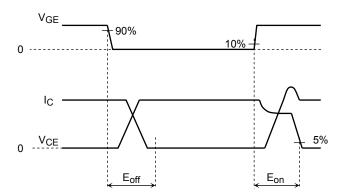
## **Electrical Characteristics (Ta = 25°C)**

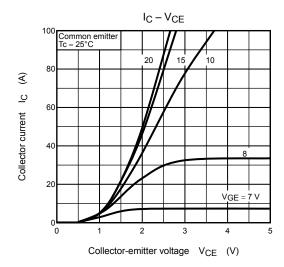
Cha	racteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current		I <sub>GES</sub>	$V_{GE} = \pm 20 \text{ V}, V_{CE} = 0$	_	_	±500	nA
Collector cut-off current		I <sub>CES</sub>	V <sub>CE</sub> = 600 V, V <sub>GE</sub> = 0	_	_	1.0	mA
Gate-emitter cut-off voltage		V <sub>GE</sub> (OFF)	$I_C = 5$ mA, $V_{CE} = 5$ V	3.5	_	6.5	V
Collector-emitter saturation voltage		V <sub>CE</sub> (sat)	$I_C = 50 \text{ A}, V_{GE} = 15 \text{ V}$	_	2.0	2.45	V
Input capacitance		C <sub>ies</sub>	$V_{CE} = 10 \text{ V}, V_{GE} = 0, f = 1 \text{ MHz}$	_	7900	_	pF
Switching time	Turn-on delay time	t <sub>d (on)</sub>	Inductive load $V_{CC}=300 \text{ V, } I_{C}=50 \text{ A}$ $V_{GG}=+15 \text{ V, } R_{G}=13 \Omega} \tag{Note 1)} (Note 2)$	_	0.09	_	μs
	Rise time	t <sub>r</sub>		_	0.07	_	
	Turn-on time	t <sub>on</sub>		_	0.24	_	
	Turn-off delay time	<sup>t</sup> d (off)		_	0.30	_	
	Fall time	t <sub>f</sub>		_	0.05	_	
	Turn-off time	t <sub>off</sub>		_	0.43	_	
Switching loss	Turn-on switching loss	E <sub>on</sub>		_	1.30	_	- mJ
	Turn-off switching loss	E <sub>off</sub>		_	1.34	_	

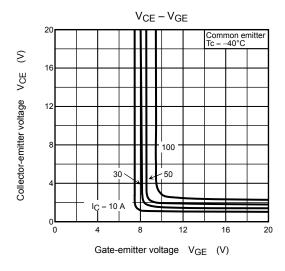
Note 1: Switching time measurement circuit and input/output waveforms

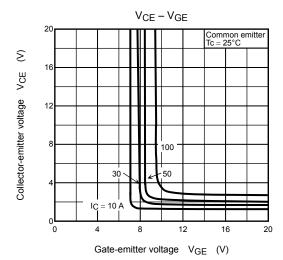


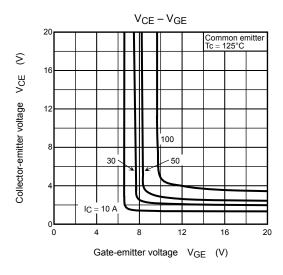
Note 2: Switching loss measurement waveforms

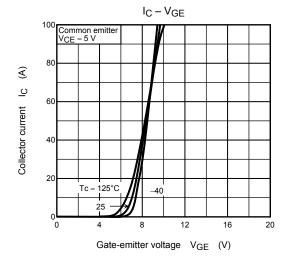


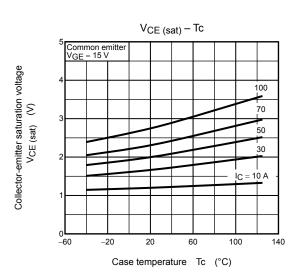




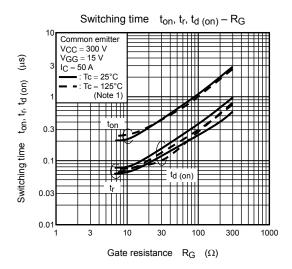


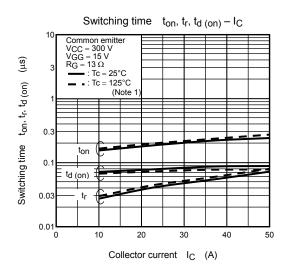


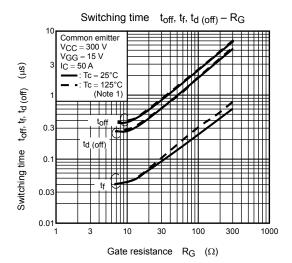


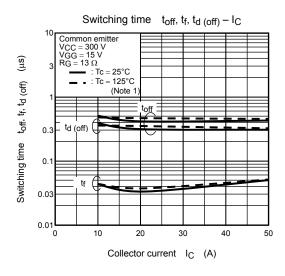


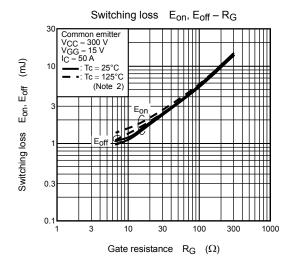
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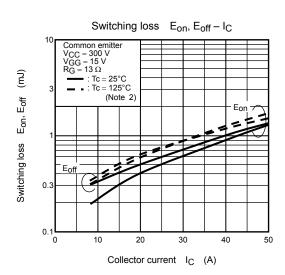


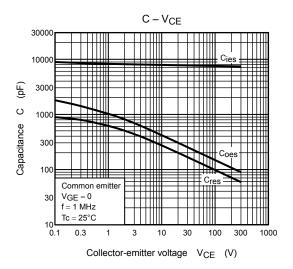


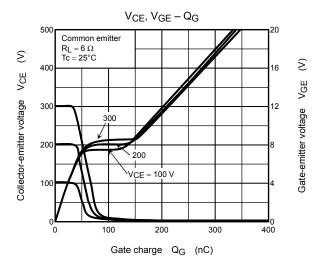


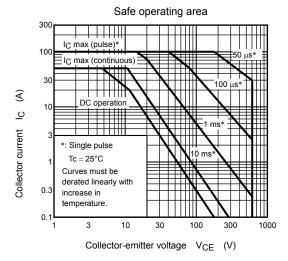


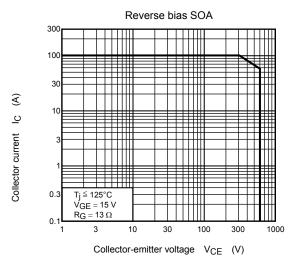


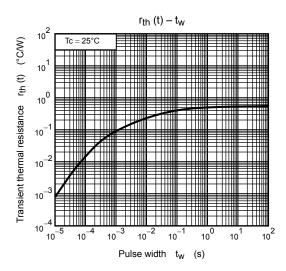












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